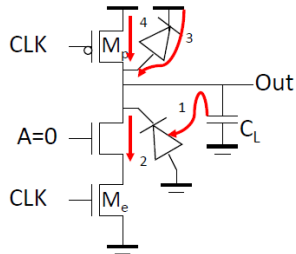


2010 VLSI Final Examination Solution

1.

(a) 2%

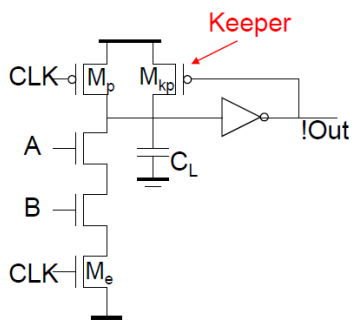


Leakage sources

→ 0.5%

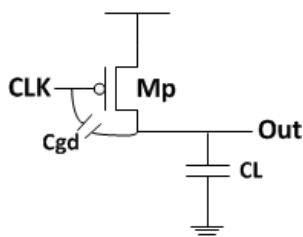
Due to charge leakage, output settles to an intermediate voltage determined by a resistive divider of the pull-up and pull-down networks. Once the output drops below the switching threshold of the fan-out logic gate, the output is interpreted as a low voltage. (0.5%)

Solution: (1%)



Keeper compensates for the charge lost due to the pull-down leakage paths.

(b) 2%



$$1.8 \times (20 + 5) = (V_x - 1.8) \times 5 + 20V_x$$

$$\rightarrow 25V_x = 54 \therefore V_x = 2.16V$$

Ans: 2.16V

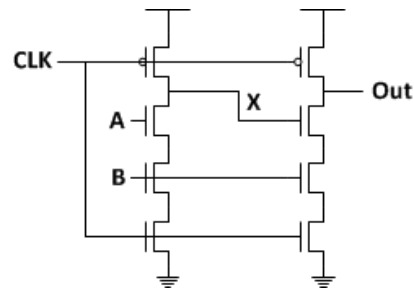
(c) 2%

$$2.16 \times 20 = V_y \times (20 + 10)$$

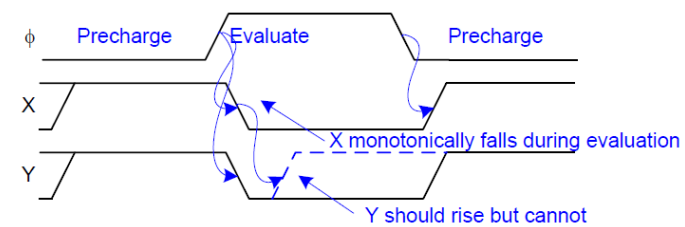
→ $V_y = 1.44V$

Ans: 1.44V

(d) 2%

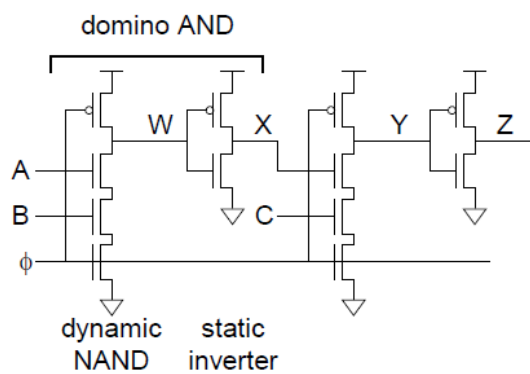


A,B=1



Dynamic gates require monotonically rising inputs during evaluation. (1%)

Solution:



(1%)

2.

Tpd(1)	A
Tcd(2)	B
Tpcq(3)	E,H
Tccq(4)	F,G
Tpdq(5)	L
Tcdq(6)	K
Tsetup(7)	C,I

Thold(8)	D,J
----------	-----

A→1	G→4
B→2	H→3
C→7	I→7
D→8	L→8
E→3	K→6
F→4	L→5

一格一分

3.

(a) 2.5%

$$T_{\text{setup}} \leq T - T_{\text{preq}} - t_{\text{plogic}}$$

(b) 2.5%

$$T_{\text{hold}} \leq T_{\text{cdreq}} + t_{\text{cdlogic}}$$

4.

(a) 2.5% (1.5% for only one correct)

With and without skew (skew-tolerant):

$$t_{pd} \leq T_c - (t_{pdq1} + t_{pdq2}) = 100ns - 2 \times 10ns = 80ns$$

(b) 2.5% (1.5% for only one correct)

Without skew:

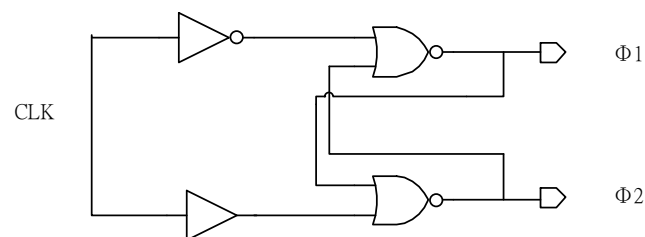
$$t_{cd} \geq T_{\text{hold}} - t_{ccq} - t_{\text{nonoverlap}} = T_{\text{hold}} - 6ns - 5ns = T_{\text{hold}} - 11ns$$

With skew:

$$t_{cd} \geq T_{\text{hold}} - t_{ccq} - t_{\text{nonoverlap}} + t_{\text{skew}} = T_{\text{hold}} - 6ns - 5ns + 2ns = T_{\text{hold}} - 9ns$$

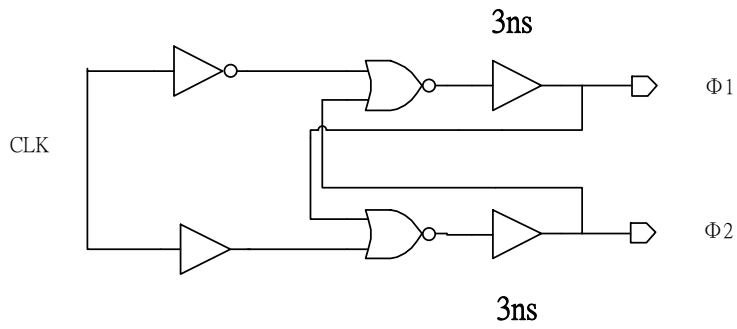
5.

(a)



3%

(b)



2%

6.

(a)

$$S = A \oplus B \oplus C_{in}$$

2%

$$C_{out} = MAJ(A, B, C_{in}) = AB + BC + CA = AB + C_{in}(A \oplus B)$$

2%

(b)

$$G = AB$$

2%

$$P = A \oplus B$$

2%

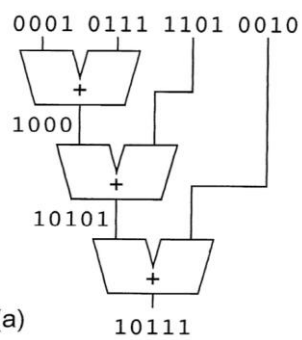
(c)

$$S = ABC_{in} + (A + B + C_{in})(\sim C_{out})$$

2%

7.

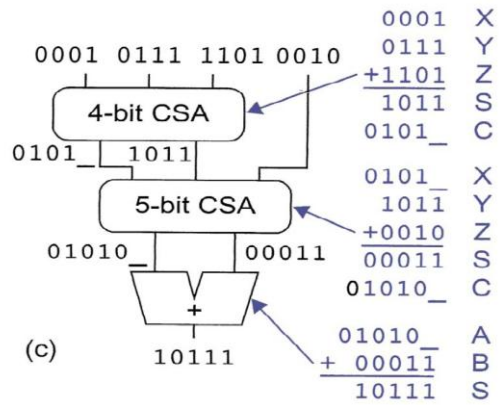
(a) 2%



Ans: 3

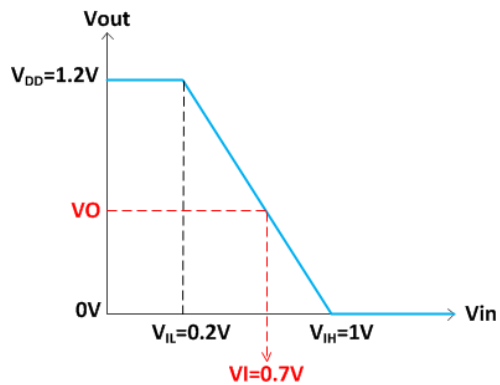
(b) 3%

Ans:



8.

(a) 2% (1% for each)



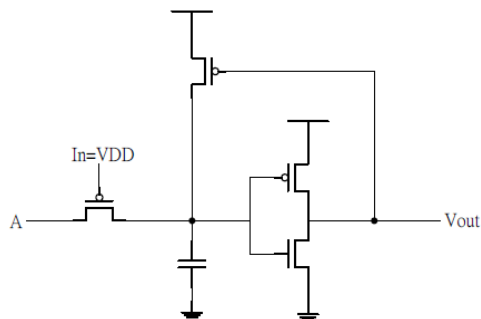
$$V_O = (1 - 0.7) \times \frac{1.2 - 0}{1 - 0.2} = 0.45V$$

Ans:

$$V_x = 0 \rightarrow 0.7V$$

$$V_{out} = 1.2 \rightarrow 0.45V$$

(b) 3%



$$1.2 \times \frac{100}{100 + R_{on}} \leq 0.2 \rightarrow R_{on} \geq 500 \text{ (ohms)}$$

Ans: 500ohms

9.

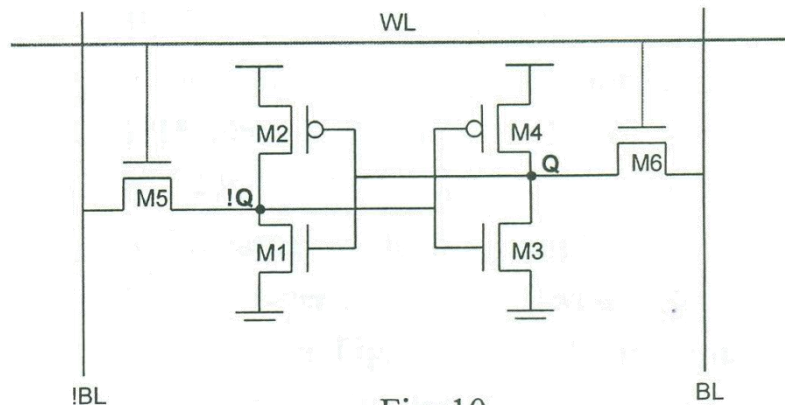


Fig. 10

(a)

Read disturb:

Assume $Q=0$, during the read operation:

\therefore BL is precharged at VDD.

\therefore Q will rise due to voltage division.

$$V_{rise} = \frac{R_{PD}}{R_{PD} + R_{PG}} \text{ 愈小愈好。}$$

$$\begin{cases} R_{PD} \propto \frac{1}{(\frac{W}{L})_{PD}} \\ R_{PG} \propto \frac{1}{(\frac{W}{L})_{PG}} \end{cases} \rightarrow \frac{(\frac{W}{L})_{PD}}{(\frac{W}{L})_{PG}} \uparrow V_{rise} \downarrow \quad 2.5\%$$

(b)

Write:

寫入”0”時，pass-gate NMOS，要和 pull-up PMOS 競爭，PG 需較強，假設 mobility

一樣， $(\frac{W}{L})_{PG} > (\frac{W}{L})_{PU}$ 。 2.5%

10.

(a)F (b)T (c)F (d)T (e)T (f)T (g)T (h)F (i)T (j)F 1% each

11.

(a) 2%(1% for each)

Bitline conditioning: Precharge bitlines high before reads.

Equalization transistor: Equalize bitlines to minimize voltage difference when using sense amplifier.

(b) 2%(1% for each)

Sense amplifier: It's invented to provide faster sensing by responding to a small voltage swing.

Isolation transistors: To Cut off large bitline capacitance when sense amplifier works.

(c) 2%(1% for each)

$$\Delta V = \frac{V_{DD}}{2} \frac{C_{cell}}{C_{cell} + C_{bit}} = 1.65 \times \frac{0.1}{1 + 0.1} = 0.15V$$

Ans:

Data 0: $1.65 - 0.15 = 1.5V$

Data 1: $1.65 + 0.15 = 1.8V$

(d) 2%(1% for each)

Add dummy lines: The dummy lines are placed at the edge because photolithography and etch problems occur most often near the edge of large repetitive structure.

ECC: Error-detecting and correcting codes are commonly used to recover from soft errors that spontaneously flip a bit store in one of the cell.

BIST: Built-in self-test that place multiplexers in the address and data paths to take over the memory during test mode.

(e) 2%(No partial)

Ans:

	B0	B1	B2	B3
WL0	1	0	1	1
WL1	0	1	1	0
WL2	1	0	1	0
WL3	1	1	1	1

(Exactly correct answers for ROM)

$$B0 = \overline{WL(1)}$$

$$B1 = \overline{WL(0) + WL(2)}$$

$$B2 = 1$$

$$B3 = \overline{WL(1) + WL(2)}$$

(These answers are also acceptable.)

12.

(a)

[False]

1%

∴ Logic level 、 fan-out 、 wire track 。

- (b)
2→1→4→3 1%
- (c)
[True] 1%
- (d)
[False] 1%
- (e)
[False] 1%
- (f)
[True] 1%
- (g)
[False] 1%
- (h)
[2] 1%
- (i)
[False] 1%
- (j)

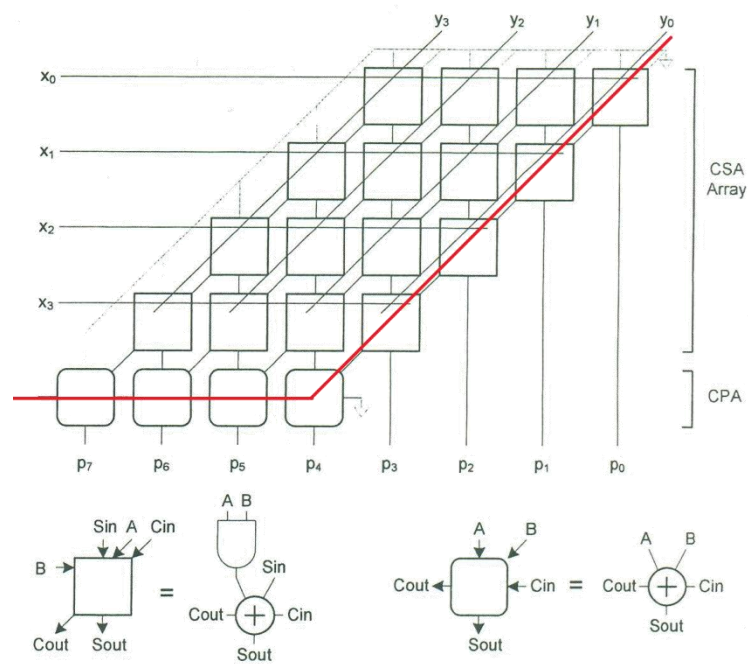


Fig. 12

1%

13.

$$G=1, B=1, H=40\text{pF}/10\text{fF}=4000$$

$$F=GBH=4000$$

(a) 2.5%

$$D_F = N \times \sqrt[N]{F}$$

N	D _F
4	31.81
5	26.27
6	23.91
7	22.89
8	22.56
9	22.62

(b) 2.5%

$$D_F = 22.56/5 = 4.512 \text{FO}_4$$

14.

(a) 2.5%

$$D_F = gh + p = 2$$

$$f_{osc} = \frac{1}{2Nd} = \frac{1}{2 \times 5 \times 2 \times RC} = \frac{1}{2 \times 5 \times 2 \times 200 \times 5f} = 50 \text{GHz}$$

(b) 2.5%

$$\begin{cases} g_u = \frac{2 + \frac{1}{2}}{2 + 1} = \frac{5}{6} \\ g_d = \frac{2 + \frac{1}{2}}{1 + \frac{1}{2}} = \frac{5}{3} \end{cases}, g_{AVG} = \frac{g_u + g_d}{2} = \frac{5}{4}$$

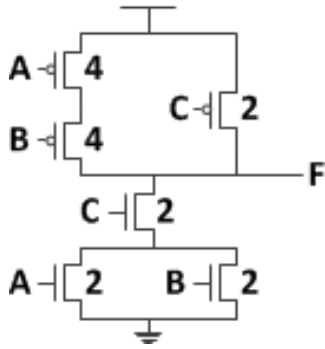
$$D_F = gh + p = 5/4 + 5/4 = 5/2$$

$$f_{osc} = \frac{1}{2Nd} = \frac{1}{2 \times 5 \times \frac{5}{2} \times RC} = \frac{1}{2 \times 5 \times \frac{5}{2} \times 200 \times 5f} = 40 \text{GHz}$$

15.

Ans:

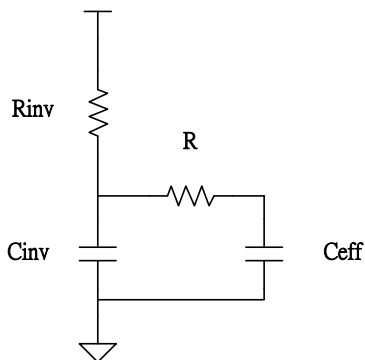
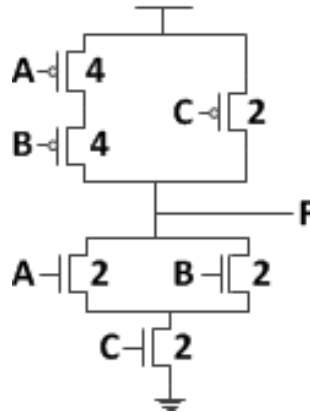
Method (1):



(a) $gA = \frac{4+2}{3} = 2, gB = \frac{4+2}{3} = 2, gC = \frac{2+2}{3} = \frac{4}{3}$ (2.5% No partial)

(b) $P = \frac{4+2+2}{3} = \frac{8}{3}$ (2.5%)

Method (2):



(a) $gA = \frac{4+2}{3} = 2, gB = \frac{4+2}{3} = 2, gC = \frac{2+2}{3} = \frac{4}{3}$

(2.5%)

(b) $P = \frac{4+2+2+2}{3} = \frac{10}{3}$ (2.5%)

16.

$R_{inv}=1k\Omega$, $C_{inv}=20fF$, $R=0.2 \times 2000=400\Omega$

$C_{adj}=0.6 \times 2000=1.2pF$, $C_{gnd}=0.4 \times 2000=0.8pF$

(a) $X=0 \rightarrow 1$, $Y=0$

$C_{eff}=C_{gnd}+C_{adj}$

$T_{pd}=R_{inv}C_{inv}+(R+R_{inv})C_{eff}=2820ps$ (2.5%)

(b) $X=0 \rightarrow 1$, $Y=1 \rightarrow 0$

$T_{pd}=R_{inv}C_{inv}+(R+R_{inv})C_{eff}=4500ps$ (2.5%)

17.

(a) 5% (No partial)

Find gavg:

$$g_u = \frac{\frac{4}{3}}{\frac{2}{3} + \frac{1}{3}} = \frac{4}{3}$$

$$g_d = \frac{\frac{4}{3}}{2 + 1} = \frac{4}{9}$$

$$g_{avg} = \frac{\frac{4}{3} + \frac{4}{9}}{2} = \frac{8}{9}$$

Find pavg:

$$p_u = \frac{6 \times \frac{4}{3} + \frac{2}{3}}{\frac{2}{3} + \frac{1}{3}} = \frac{26}{3}$$

$$p_d = \frac{6 \times \frac{4}{3} + \frac{2}{3}}{2 + 1} = \frac{26}{9}$$

$$p_{avg} = \frac{\frac{26}{3} + \frac{26}{9}}{2} = \frac{52}{9}$$

Find path delay:

$$G = 1 \times \frac{8}{9} = \frac{8}{9}$$

$$F = GBH = \frac{8}{9} \times 1 \times \frac{60}{2} = \frac{80}{3}$$

$$P = 1 + \frac{52}{9} = \frac{61}{9}$$

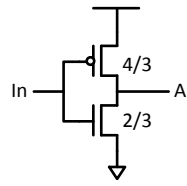
$$N = 2$$

$$D = 2 \times \sqrt{\frac{80}{3}} + \frac{61}{9} = \frac{61 + 24\sqrt{15}}{9} = 17.106$$

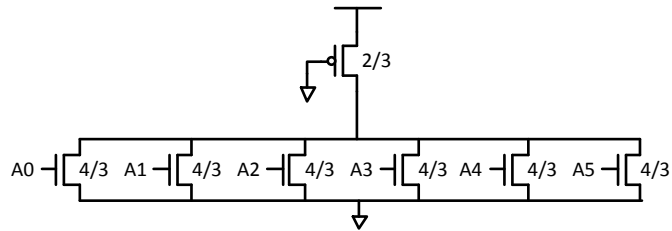
Ans: 17.106 (Time Unit)

(b) 5%

Ans 1:



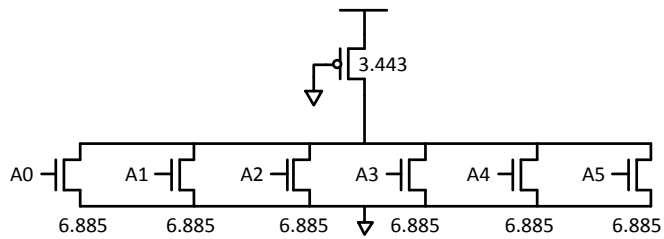
(0%)



Ans 2:

$$f = \sqrt{F} = \sqrt{\frac{80}{3}} = gh = \frac{8}{9} \times \frac{60}{x}$$

$$\rightarrow x = 10.328$$



$$\text{PMOS: } 10.328 \times \frac{\frac{2}{3}}{\frac{2}{3} + \frac{4}{3}} = 3.443$$

$$\text{NMOS: } 10.328 \times \frac{\frac{4}{3}}{\frac{2}{3} + \frac{4}{3}} = 6.885$$